SILICON (Si) POWER MOSFET ▲ CEB60N06G



CEB60N06G

60V ▲ 13mΩ ▲ 60A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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RoHS

REACH

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _c = 25°C	I _D	60A
Pulsed Drain Current Note 1	IDM Note 5	240A
Maximum Power Dissipation at T _c = 25°C	PD	125W
Power Dissipation Derating above 25°C	ΔP _D	0.83W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	360mJ
Single Pulsed Avalanche Current Note 4	I _{AS}	30A
Operating and Storage Temperature Range	Т _Ј , Т _{STG}	-65°C to +175°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	1.2°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH_JA}	62.5°C/W

APPLICATIONS

Battery Management	DC/DC	DC	Industrial	Power
Systems	Converter	Fan	Control	Switches
+ -				

PIN DESCRIPTION

Circuit Diagram	Outline - Bottom View	Pin No.	Description
D (1)		1	Drain
G (3)		2	Source
S (2)		3	Gate

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ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV _{DSS}	60			V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	2		4	V
Static Drain-Source On-Resistance	V_{GS} = 10V, I _D = 24A	R _{DS(ON)}		13	16	mΩ
Dynamic Characteristics Note 3						
land Constitution		C		2045		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$ $V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	CISS		2015 495		рF
Output Capacitance	55 - , 65 - ,	C _{oss}				рF
Reverse Transfer Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	C _{RSS}		55		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 15A, $R_{G(ext)}$ = 4.7 Ω	t _{D(ON)}		22	44	ns
Turn-On Rise Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 15A, $R_{G(ext)}$ = 4.7 Ω	t _R		17	34	ns
Turn-Off Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 15A, $R_{\text{G(ext)}}$ = 4.7 Ω	$t_{D(OFF)}$		47	94	ns
Turn-Off Fall Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 15A, $R_{\text{G(ext)}}$ = 4.7 Ω	t _F		18	36	ns
Total Gate Charge	$V_{DS} = 48V, V_{GS} = 10V, I_D = 75A$	Q _G		52	68	nC
Gate Source Charge	$V_{DS} = 48V, V_{GS} = 10V, I_D = 75A$	Q _{GS}		11		nC
Gate Drain Charge	$V_{DS} = 48V, V_{GS} = 10V, I_{D} = 75A$	Q_{GD}		18		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I _S			60	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 24A	V_{SD}			1.3	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

3: Guaranteed by design, not subject to production testing.

4: L = 0.8 mH, $I_{AS} = 30 \text{A}$, $V_{DD} = 30 \text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25 ^{\circ}\text{C}$.

5: Pulse width limited by safe operating area.

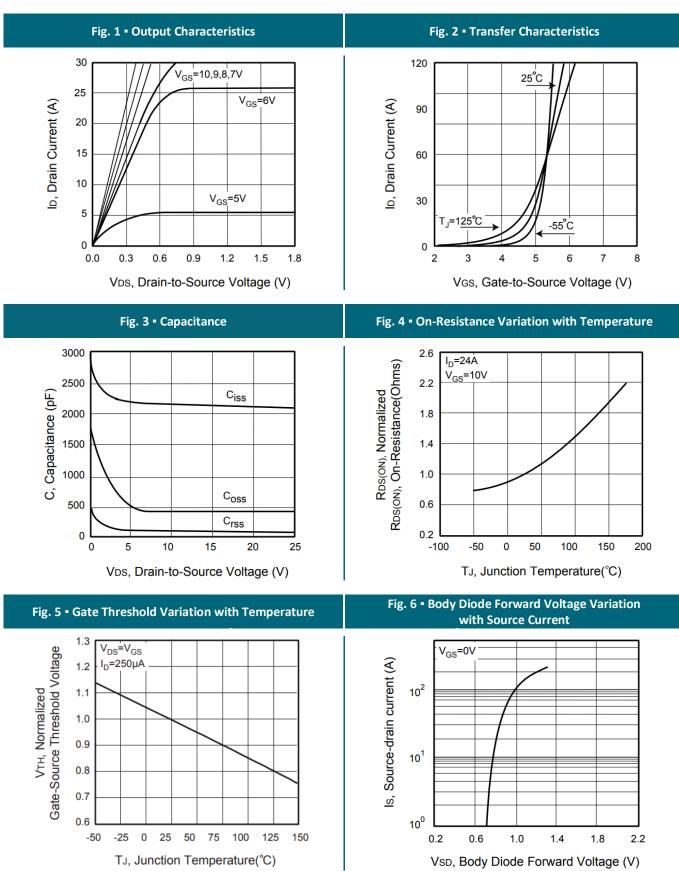
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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

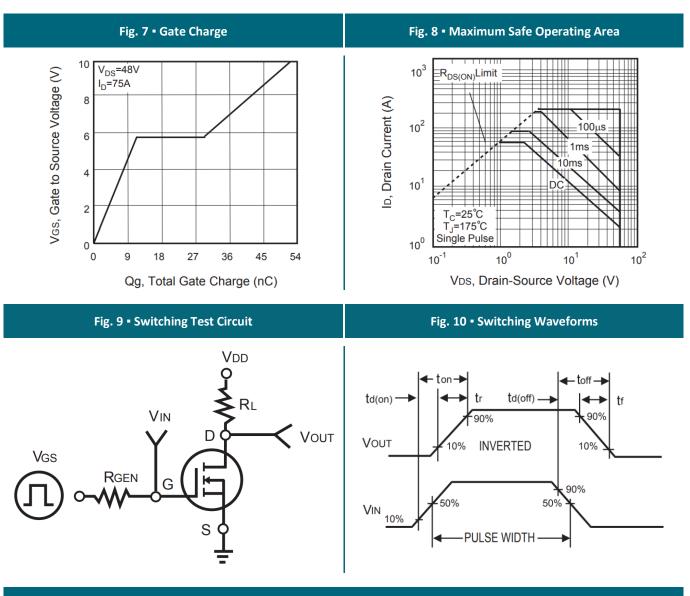
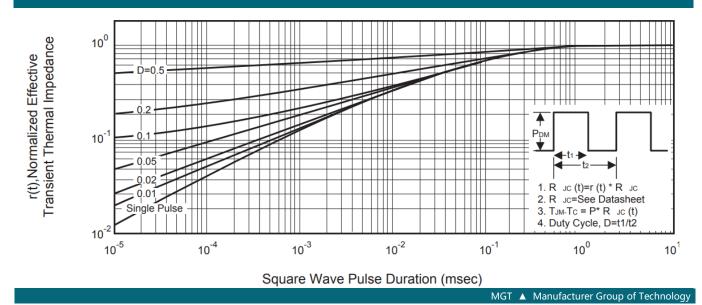


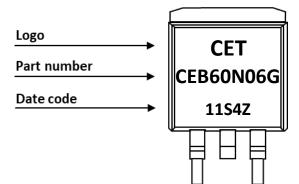
Fig. 11 • Normalized Thermal Transient Impedance Curve



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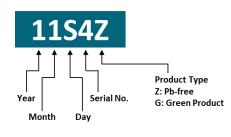






DATE CODE

Example: 11S4Z



Coding list for "Day"

1	2	3	4	5	6	7	8	9	A
01	02	03	04	05	06	07	08	09	10
B	C	D	E	F	G	H	┃	J	K
11	12	13	14	15	16	17	18	19	20
L	M	N	O	P	Q	R	S	T	U
21	22	23	24	25	26	27	28	29	30
V 31									

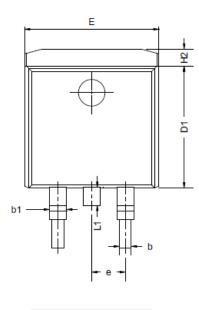
Coding list for "Month"

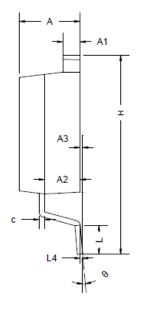
	1 an	2 Feb	3 Mar	4 Apr	5 May	6 Jun				
	7 ul	8 Aug	9 Sep	A Oct	B Nov	C Dec				
Coding list for "Year"										
	0	1	L 2	2 3	34	1				
	202	0 20	21 20	22 20	023 20	24				
	5	e	5 7	7 8	<u> </u>	•				
	202	5 20	26 20	27 20	028 20	29				

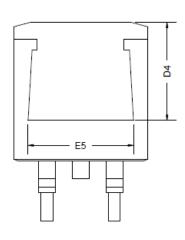
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PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	E	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
с	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

ORDERING INFORMATION

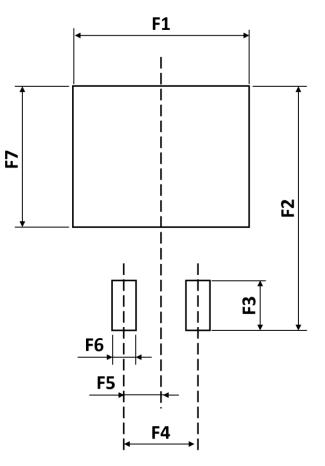
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB60N06G	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs

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RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

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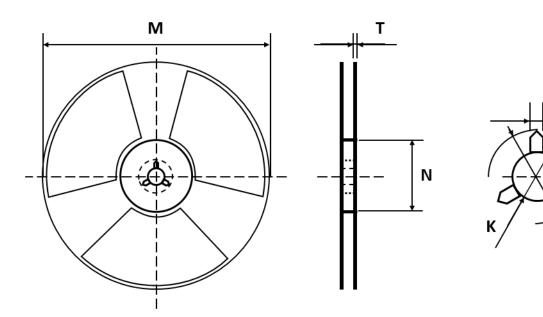


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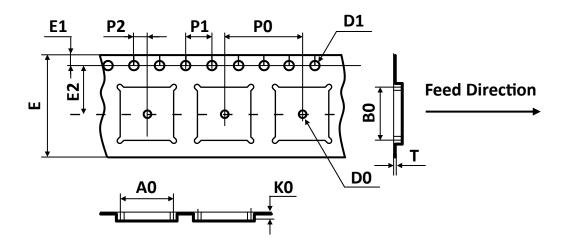


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS All dimensions in mm



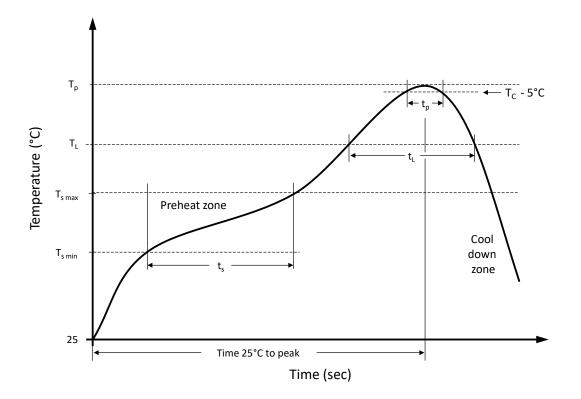
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05



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RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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